TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

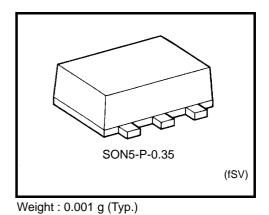
# TC7SH34FS

#### **NON-INVERT BUFFER**

#### **Features**

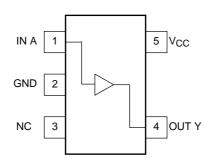
High speed:  $t_{pd}=3.8$  ns (typ.) at  $V_{CC}=5$  V Low power dissipation:  $I_{CC}=2$   $\mu A$  (max) at Ta = 25°C High noise immunity:  $V_{NIH}=V_{NIL}=28\%$   $V_{CC}$  (min) 5.5V tolerant input.

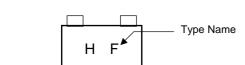
Wide operating voltage range: V<sub>CC</sub> (opr) = 2~5.5 V



# Marking (top view)

## · Pin Assignment





## **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	-0.5~7.0	V
DC input voltage	V <sub>IN</sub>	-0.5~7.0	V
DC output voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> + 0.5	V
Input diode current	I <sub>IK</sub>	-20	mA
Output diode current	lok	±20	mA
DC output current	lout	±25	mA
DC V <sub>CC</sub> /ground current	Icc	±50	mA
Power dissipation	PD	50	mW
Storage temperature	T <sub>stg</sub>	-65~150	°C

## Logic Diagram



### **Truth Table**

А	Υ
L	L
Н	Н

## **Recommended Operating Conditions**

Characteristics	Symbol	Rating	Unit	
Supply voltage	V <sub>CC</sub>	2.0~5.5	V	
Input voltage	V <sub>IN</sub>	0~5.5	<b>V</b>	
Output voltage	V <sub>OUT</sub>	0~Vcc	V	
Operating temperature	T <sub>opr</sub>	-40~85	°C	
Input rise and fall time	dt/dv	$0 \sim 100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{ V)}$	ns/V	
input rise and fail time	ui/uv	$0 \sim 20 \; (V_{CC} = 5 \pm 0.5 \; V)$	115/ V	

#### **Electrical Characteristics**

#### **DC Characteristics**

Characteristics Symbol Test Circuit		Test				Ta = 25°C			Ta = -40~85°C		
		Test Condition		V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit	
LP-sh Javas Carret				2.0	1.50	_	_	1.50	_	V	
High-level input voltage	V <sub>IH</sub>	_	_		3.0~ 5.5	V <sub>CC</sub> × 0.7	_	_	V <sub>CC</sub> × 0.7		_
Low-level input					2.0	_	_	0.50	_	0.50	
voltage	V <sub>IL</sub>	_		_	3.0~ 5.5	_	_	V <sub>CC</sub> × 0.3	_	V <sub>CC</sub> × 0.3	V
		_	V <sub>IN</sub> = V <sub>IH</sub>	Ι <sub>ΟΗ</sub> = -50 μΑ	2.0	1.9	2.0	_	1.9	_	V
					3.0	2.9	3.0	_	2.9	_	
High-level output voltage	VoH				4.5	4.4	4.5	_	4.4	_	
			I <sub>OH</sub> = -4 mA	3.0	2.58	_	_	2.48	_		
				I <sub>OH</sub> = -8 mA	4.5	3.94	_	_	3.80	_	
					2.0	_	0.0	0.1	_	0.1	
Low-level output voltage V <sub>OL</sub> -		V <sub>IN</sub> = V <sub>IL</sub>	I <sub>OL</sub> = 50 μA	3.0	_	0.0	0.1	_	0.1	V	
				4.5	_	0.0	0.1	_	0.1		
			I <sub>OL</sub> = 4 mA	3.0	_	_	0.36	_	0.44		
				I <sub>OL</sub> = 8 mA	4.5	_	_	0.36	_	0.44	
Input leakage current	I <sub>IN</sub>	_	V <sub>IN</sub> = 5.5 V or GND		0~ 5.5	_	_	±0.1	_	±1.0	μА
Quiescent supply current	Icc	_	V <sub>IN</sub> = V <sub>CC</sub> or GND			_	_	2.0	_	20.0	μА

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#### AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$ )

Characteristics Symbol	Test Circuit	Test Condition		Ta = 25°C			Ta = -40~85°C		Unit		
			V <sub>CC</sub> (V)	C <sub>L</sub> (pF)	Min	Тур.	Max	Min	Max	Offic	
Propagation delay <sup>†</sup> pLH time <sup>†</sup> pHL			3.3 ± 0.3	15	_	5.0	7.1	1.0	8.5	- ns	
				50	_	7.5	10.6	1.0	12.0		
	t <sub>pHL</sub>		5.0 ± 0.5	15	_	3.8	5.5	1.0	6.5		
		3.0 ± 0.	5.0 ± 0.5	50	_	5.3	7.5	1.0	8.5		
Input capacitance	C <sub>IN</sub>	_		_		_	4	10	_	10	pF
Power dissipation capacitance	C <sub>PD</sub>	_			(Note)		13		_		pF

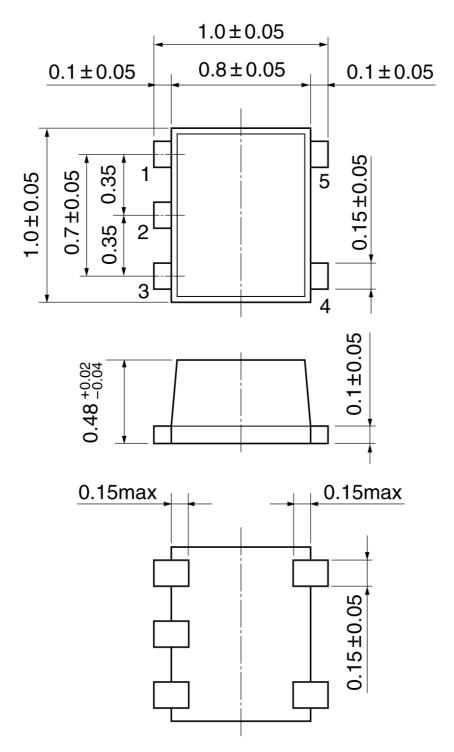
Note: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

### **Package Dimensions**

SON5-P-0.35 Unit:mm



Weight: 0.001 g (typ.)

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